

**AMENDMENTS**

***In The Claims***

Please add new claims 22-~~36~~<sup>34</sup>, as provided in the APPENDIX A attached hereafter. The entire set of the pending claims is provided in the APPENDIX B attached hereafter.


**REMARKS**

In this amendment, claims 22-34 have been newly added. Claims 18 and 22-34 are now active in this application, of which claims 18, 22 and 30 are independent.

If the Examiner believes, for any reason, that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at the number provided.

Prompt and favorable consideration of this Amendment is respectfully requested.

Respectfully submitted,

  
Hae-Chan Park  
Reg. No. 50,114

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McGuire Woods LLP  
1750 Tysons Boulevard  
Suite 1800  
McLean, VA 22102-4215  
Tel: 703-712-5000  
Fax: 703-712-5050  
HCP:WSC/kbs

## APPENDIX A

Please add new claims 22-34, as follows.

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22. (Newly added) A deposition apparatus, comprising:  
a deposition chamber for depositing a doped amorphous silicon layer on a substrate;  
a sputter chamber for depositing a metal layer on the doped amorphous silicon layer; and  
a vacuum passage for transferring the substrate in a vacuum from said deposition chamber to said sputter chamber to prevent oxidization of an upper surface of the doped amorphous silicon layer.
23. (Newly added) The deposition apparatus of claim 22, wherein said deposition chamber is a CVD (chemical vapor deposition) chamber.
24. (Newly added) The deposition apparatus of claim 23, further comprising another CVD chamber for depositing a gate insulating layer, an amorphous silicon layer on the substrate prior to depositing the doped amorphous silicon layer.
25. (Newly added) The deposition apparatus of claim 24, wherein the gate insulating layer is formed at a thickness between 3000 Å to 6000 Å, the amorphous silicon layer is formed at a thickness between 1000 Å to 3000 Å, and the doped amorphous silicon layer is formed at a thickness of 200 Å to 1000 Å.

26. (Newly added) The deposition apparatus of claim 24, further comprising a preheat chamber for heating the substrate prior to depositing the gate insulating layer and the amorphous silicon layer.

27. (Newly added) The deposition apparatus of claim 24, further comprising a load lock chamber for receiving the substrate.

28. (Newly added) The deposition apparatus of claim 22, wherein the substrate has a gate wire layer formed thereon.

29. (Newly added) The deposition apparatus of claim 22, wherein the metal layer comprises chromium (Cr).

30. (Newly added) The deposition apparatus, comprising:  
a load lock chamber for receiving a substrate;  
a preheat chamber for heating the substrate;  
a deposition chamber for depositing a doped amorphous silicon layer on the substrate;  
a sputter chamber for depositing a metal layer on the doped amorphous silicon layer; and  
a vacuum passage for transferring the substrate in a vacuum from said deposition chamber to said sputter chamber to prevent oxidization of an upper surface of the doped amorphous silicon layer.

31. (Newly added) The deposition apparatus of claim 30, wherein the substrate has a gate wire pattern formed thereon.

32. (Newly added) The deposition apparatus of claim 31, further comprising another deposition chamber for depositing a gate insulating layer and an amorphous silicon layer on the gate wire pattern prior to depositing the doped amorphous silicon layer.

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33. (Newly added) The deposition apparatus of claim 30, wherein the deposition chamber is a chemical vapor deposition (CVD) chamber.

34. (Newly added) The deposition apparatus of claim 31, wherein the metal layer comprises chromium (Cr).

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